

Antonio Pio Catalano

Tutor: Prof. Vincenzo d'Alessandro

XXXII Cycle - I year presentation

Thermal analyses of electronic
devices for RF and Power applications



Background

M.Sc.

Electronic Engineering –
October 27th 2016

Subject : **Microelectronics,**
Prof. *Vincenzo d'Alessandro*

Title: *Numerical Optimization
of GaAs HBT Thermal
Ruggedness with Design Of
Experiments*

Ph.D.

Electronic Group – **Ing-Inf/01**

Prof. **d'Alessandro**, Prof. **Rinaldi**

Athenaeum fellowship

**RF devices characterization
laboratory**, building 2, Via
Claudio.

Tel. +39 081 73 **86145**

Cooperations

Politecnico di Milano

Prof. Lorenzo Codecasa



Qorvo Inc.

qorvoTM

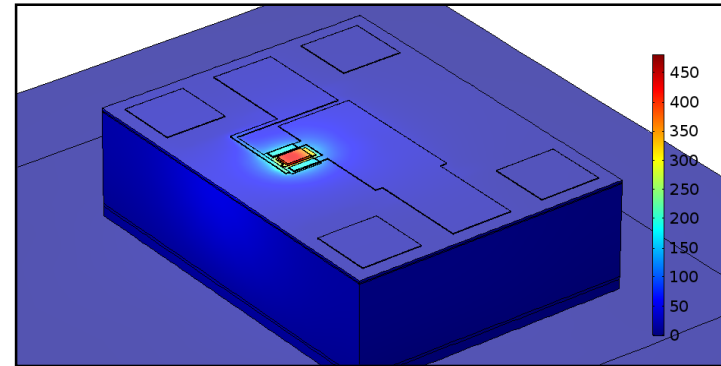
*Peter J. Zampardi (Newbury
Park, CA, USA)*

*Brian Moser (Thorndike Rd.
Greensboro, NC, USA)*

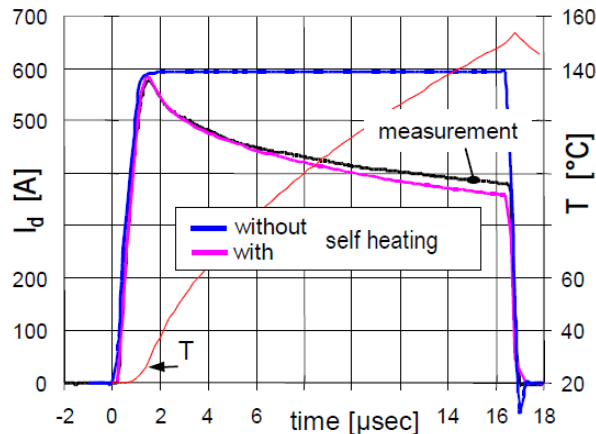
High-accurate thermal analyses

Study thermal performance:

- Impact on SOA
- Technology, layout and package design

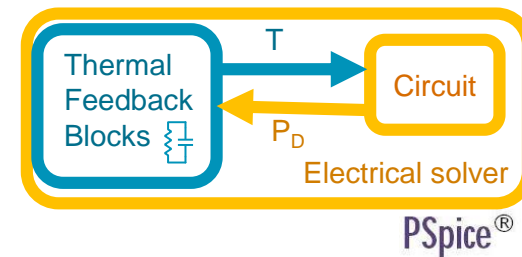


Electrothermal simulations:

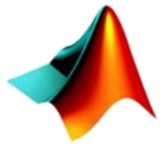
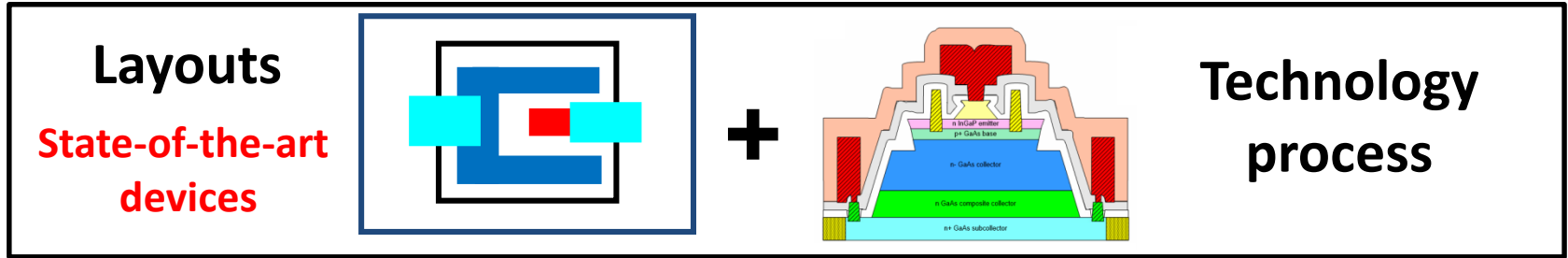


By ET analyses is possible:

- to include the **self-heating effects**
- to evaluate the **real performance**
- to study **breakdown effects**

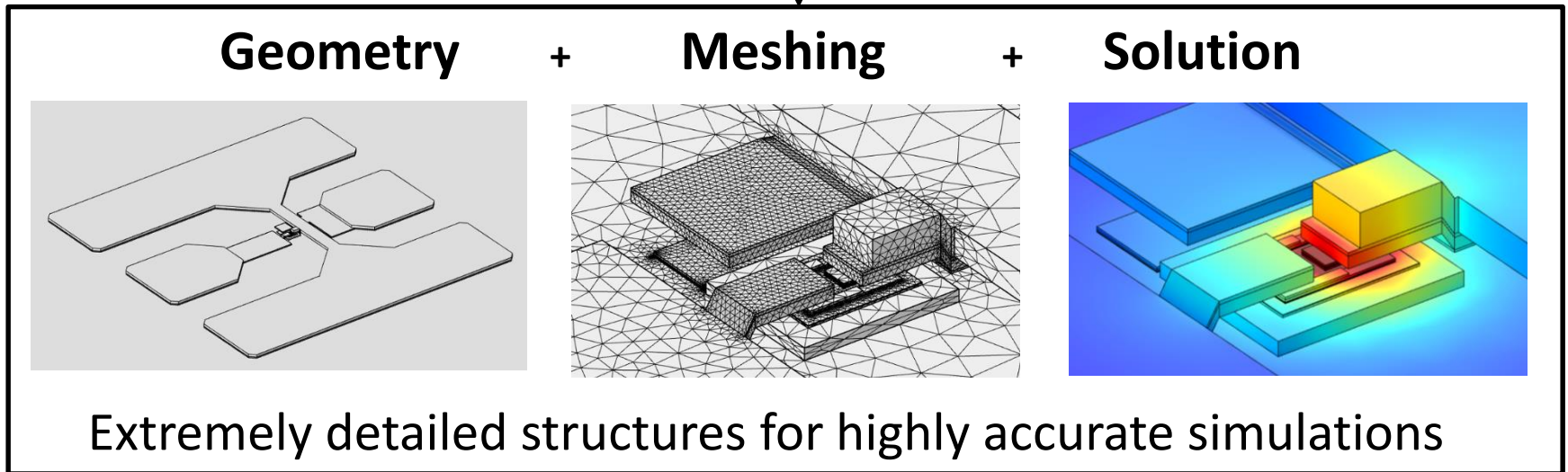


FEM purely-thermal simulation tool



MATLAB

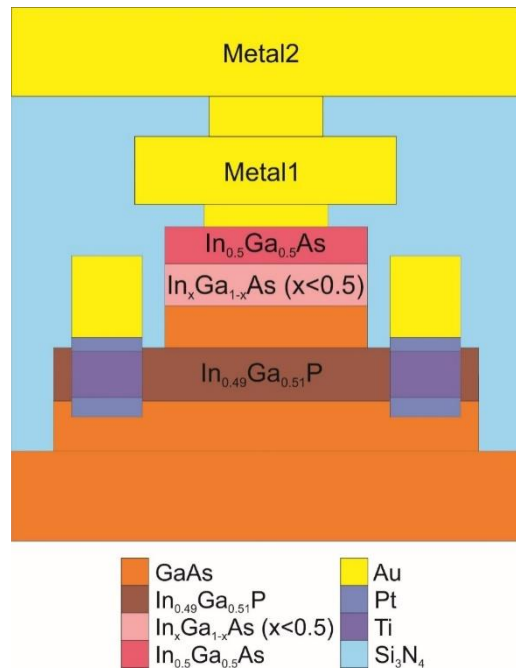
Automatically



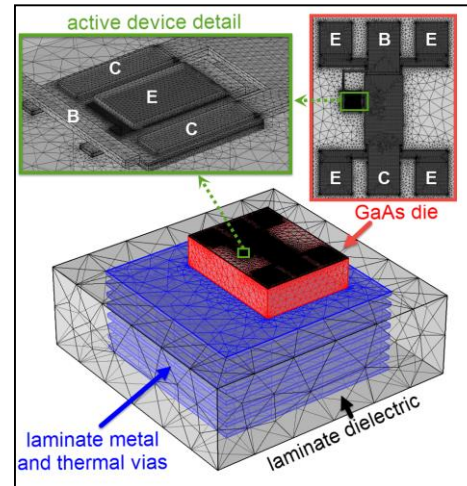
Devices for RF applications

GaAs-based Heterojunction Bipolar Transistors (HBTs)

Impact of semiconductor and metal layers on R_{th}

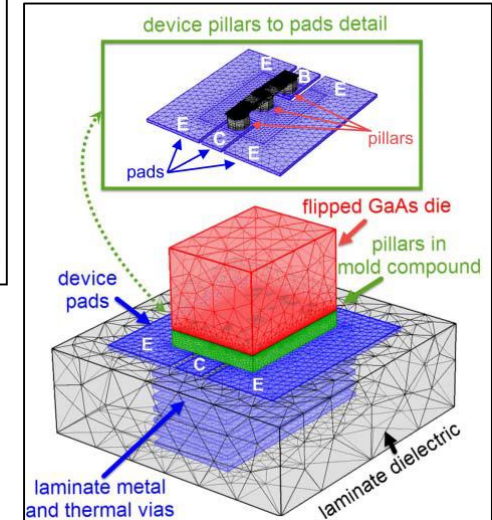


Impact of packaging styles on R_{th}



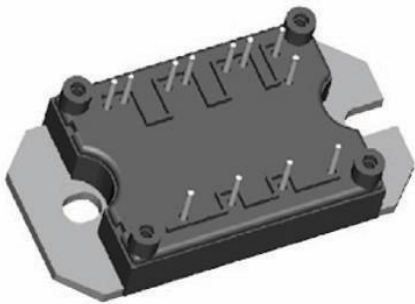
← wire bonding

flip-chip →

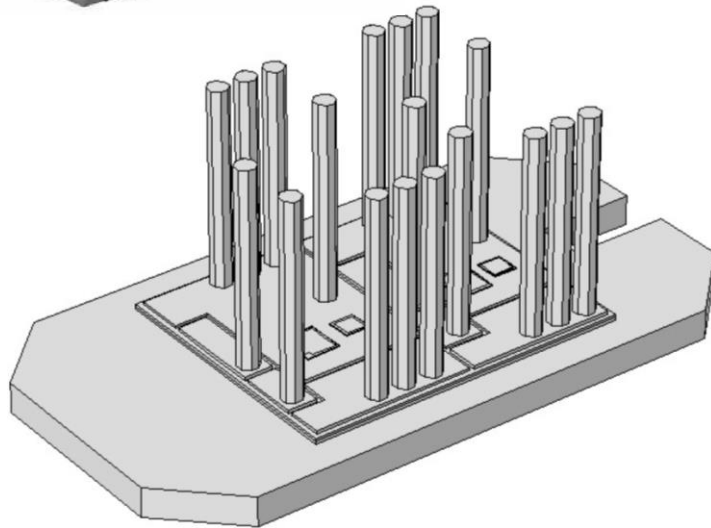


Devices for Power applications

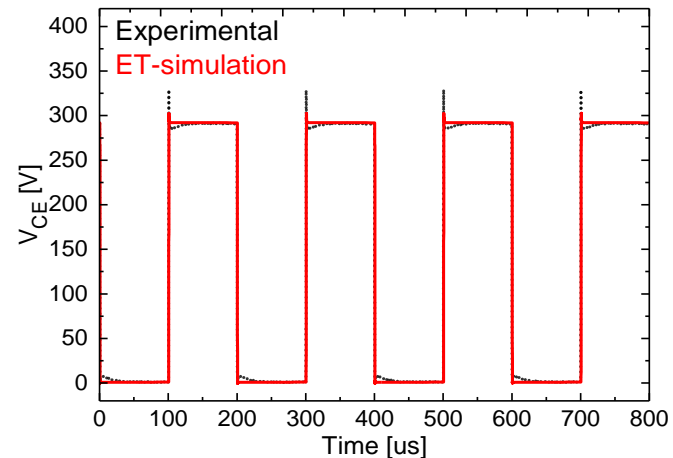
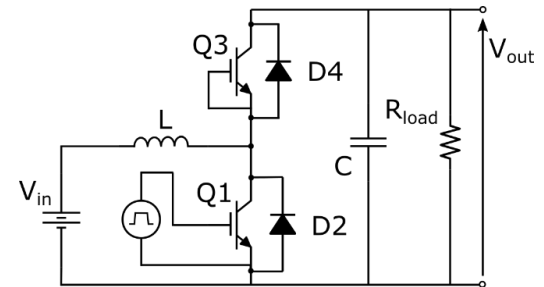
IGBT module in MTP package – thermal feedback block extraction



3D model
TFB extraction



Circuit-level
ET simulations
(Buck converter)



Agreement with **experimental** results

1st year production

Journal Papers	<p>V. d'Alessandro <i>et al.</i>, "Simulation comparison of InGaP/GaAs HBT thermal performance in wire-bonding and flip-chip technologies," <i>Microelectronics Reliability</i>, vol. 78, pp. 233-242, 2017.</p>
Conference Papers	<p>A. P. Catalano <i>et al.</i>, "Influence of layout and technology parameters on the thermal behavior of InGaP/GaAs HBTs," in <i>Proc. IEEE 13th Ph. D. Research in Microelectronics and Electronics (PRIME)</i>, Jun. 2017.</p> <p>A. P. Catalano <i>et al.</i>, "Numerical analysis of the thermal behavior sensitivity to technology parameters and operating conditions in InGaP/GaAs HBTs," in <i>Proc. IEEE Compound Semiconductor Integrated Circuit Symposium (CSICS)</i>, Oct. 2017.</p> <p>A. P. Catalano <i>et al.</i>, "Model-Order Reduction Procedure for Fast Dynamic Electrothermal Simulation of Power Converters," in <i>Proc. Applications in Electronics Pervading Industry, Environment and Society (APPLEPIES)</i>, Sep. 2017.</p> <p>A. P. Catalano <i>et al.</i>, "Effect of heat source modeling in DC circuit-level electrothermal simulation of power MOSFETs," in <i>Proc. 49th SIE conference</i>, 2017.</p> <p>V. d'Alessandro <i>et al.</i>, "Combined SPICE-FEM Analysis of Electrothermal Effects in InGaP/GaAs HBT Arrays for Handset Applications," in <i>Proc. IEEE 19th Thermal, Mechanical and Multi-Physics Simulation and Experiments in Microelectronics and Microsystems (EuroSimE)</i>, Apr. 2018. (accepted as Keynote presentation)</p>

Next years...

Research activity:

- Extend the purely-thermal simulations for **ET stationary analyses of GaAs HBTs**
- **ET analyses for photovoltaic fields**
- Thermal evaluation of **packaging techniques for Power modules**

Conferences and PhD schools:

- **EuroSimE** conference, Toulouse, France, April 15th-18th 2018
- **Società Italiana Elettronica**, Conference and PhD school, Napoli, Italy, June 18th-22th 2018

Credits summary :

Student: Antonio Pio Catalano
antonio.pio.catalano@unina.it

Tutor: Prof. Vincenzo d'Alessandro
vindales@unina.it

Cycle XXXII

	Credits year 1								Credits year 2								Credits year 3								Total	Check
	Estimated	1	2	3	4	5	6	Summary	Estimated	1	2	3	4	5	6	Summary	Estimated	1	2	3	4	5	6	Summary		
Modules	20	3	0	0	0	3	9	15	10							0	0							0	15	30-70
Seminars	5	1,9	0	0	3	0,8	0,3	6	5							0	0							0	5,7	10-30
Research	35	5,1	10	10	5	5,2	3,7	39	45							0	60							0	39	80-140
	60	10	10	10	8	9	13	60	60	0	0	0	0	0	0	0	60	0	0	0	0	0	0	0	60	180

Thank you for your kind attention